
Bias Voltage DAC Operating at Cryogenic Temperatures for Solid-State Qubit Applications

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Outline

- Motivation: quantum computers & cryogenic electronics
 - Requirements for GaAs spin qubit biasing
- Prototype IC for local cryogenic qubit biasing (Bias DAC)
 - Topology
 - Coarse tuning reference voltages
 - Benefits and calibration method
 - Bias DAC results
 - Auxiliary circuits results
 - OpAmp buffer
 - $\Sigma\Delta$ modulator
- Summary & Outlook

Quantum Computers

- Possible **exponential speed up** for certain tasks:
 - Shor's algorithm for **factoring integers**
 - Grover's algorithm for **search in unordered databases**
 - **Quantum chemistry**: Simulate new molecules and catalysts
 - Quantum(-enhanced) machine learning

- Requirements for a universal quantum computer:
 - **Large number (10^6 - 10^8) of physical qubits**^[1] (operated at $T \lesssim 1K$)
 - Room temperature electronics to communicate with the qubits
 - **Scalable control and read-out electronics**

[1] Vandersypen, L.M.K., Bluhm, H., Clarke, J.S. et al. Interfacing spin qubits in quantum dots and donors—hot, dense, and coherent. *npj Quantum Inf* **3**, 34 (2017). <https://doi.org/10.1038/s41534-017-0038-y>

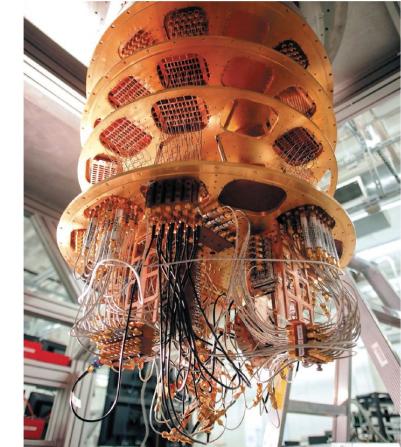
Quantum Computers

- 'Brute force' scaling to operate up to 50-100 qubits
- Further scaling very difficult
- The 'Tyranny of numbers' (Jack Morton, Bell Labs, 1958) is back
- **Let's solve it (again) with integrated circuits**

Today

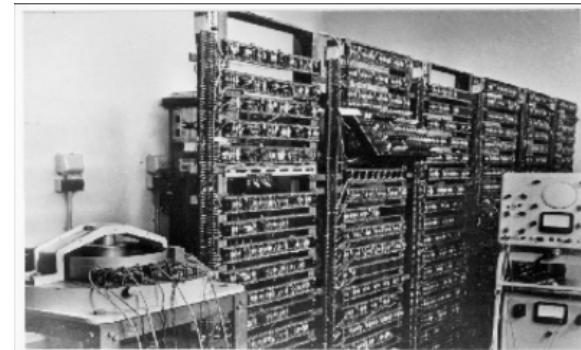


Source: IBM

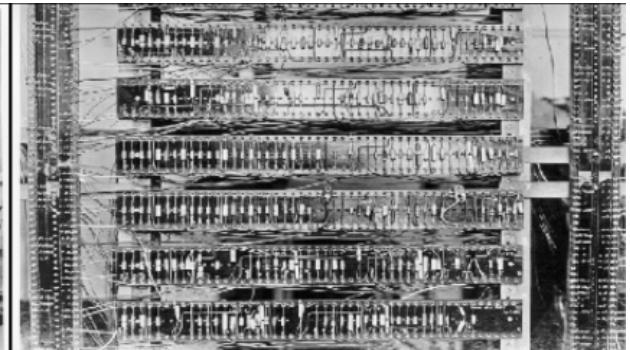


Source: Google, Mohseni et al., Nature 543 (2017)

1950s



Source: IBM



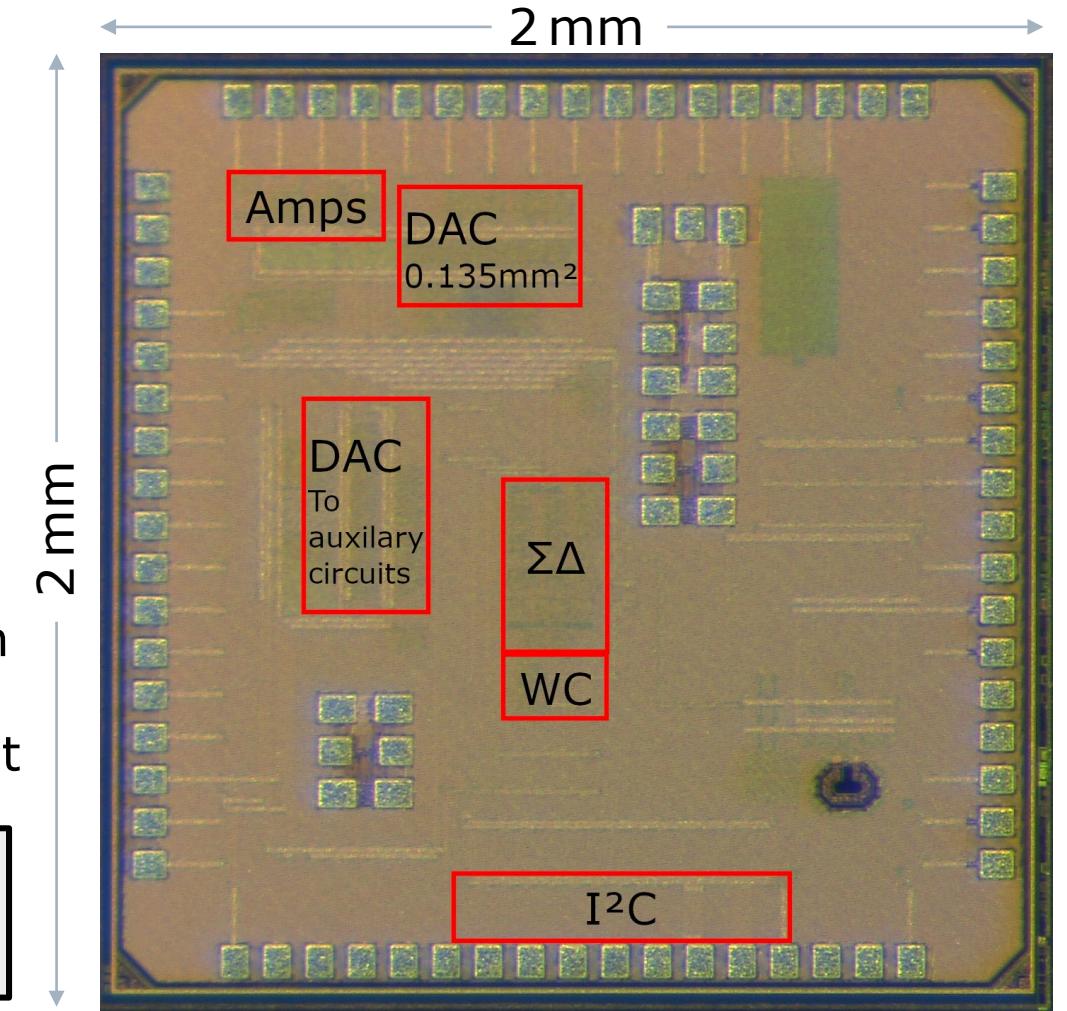
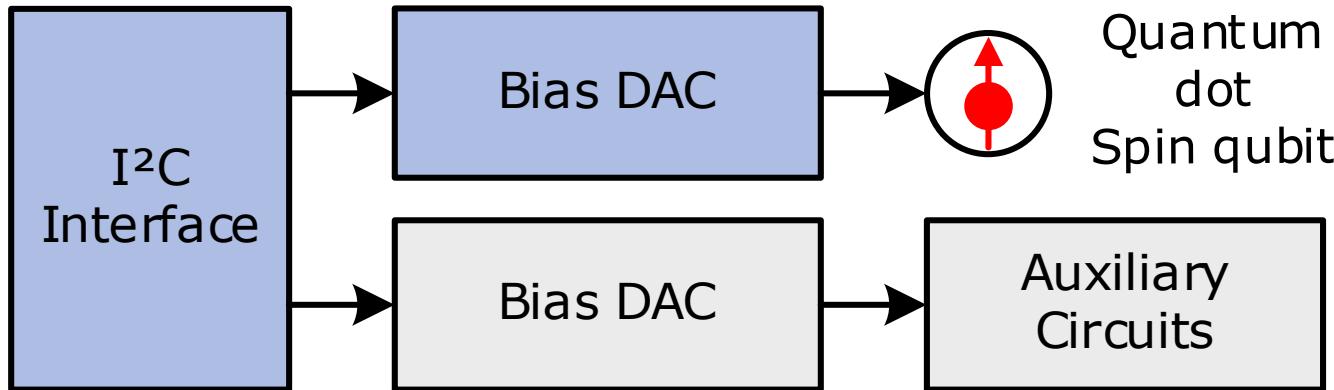
Requirements GaAs Spin Qubit

Characteristic	Specification
Bias voltage range	-1 V to 0 V
Bias voltage noise v_{RMS}	$\lesssim 20 \mu\text{V}$
Bias voltage step size	$250 \mu\text{V} (\triangleq 12 \text{ bit})$
Operating temperature	100 mK
Cooling power budget @ 100 mK	<1 mW

- Up to 8 uncorrelated bias voltages per qubit
 - Forming potential wells
- Key performance indicator: fidelity of qubit gate

Prototype IC

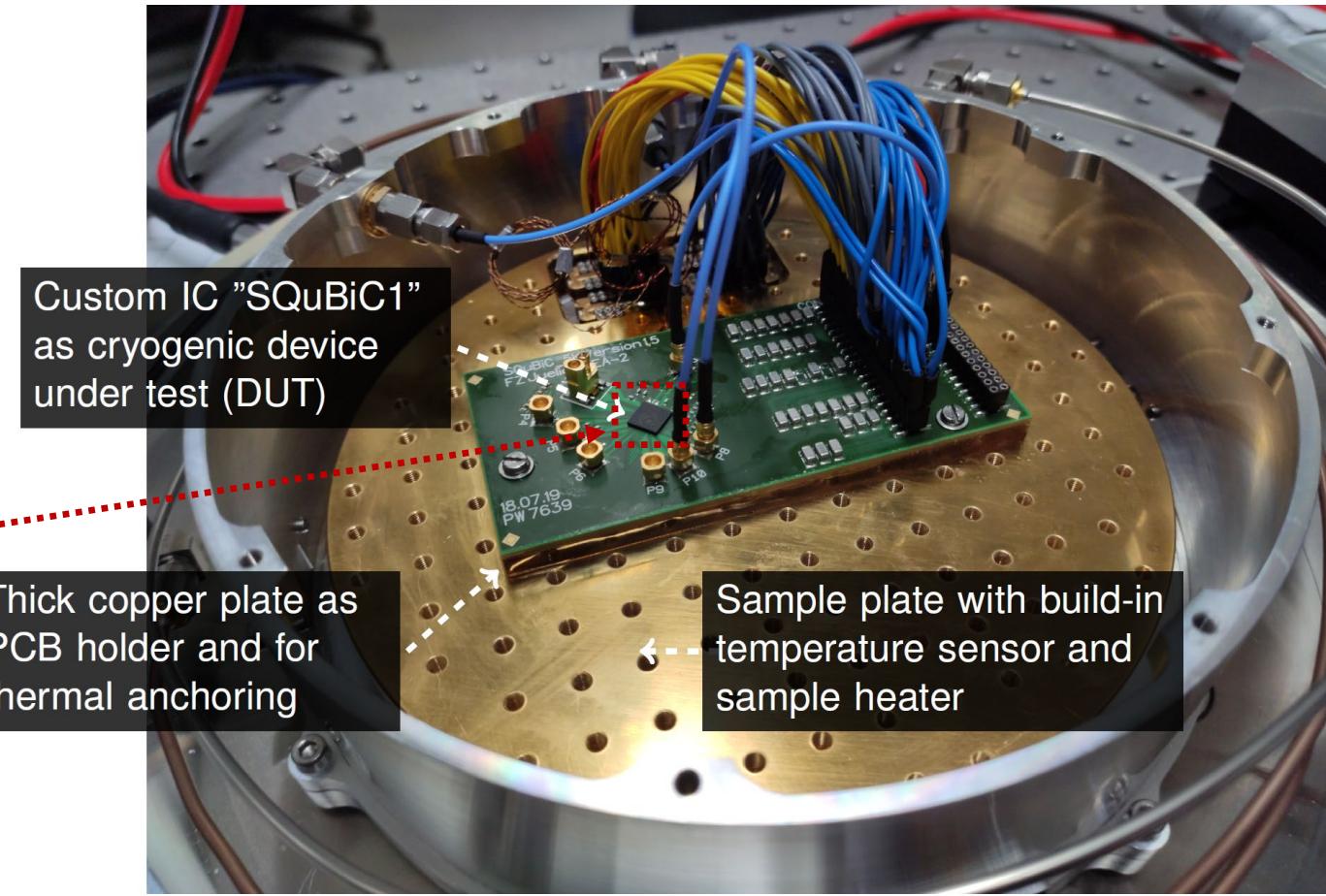
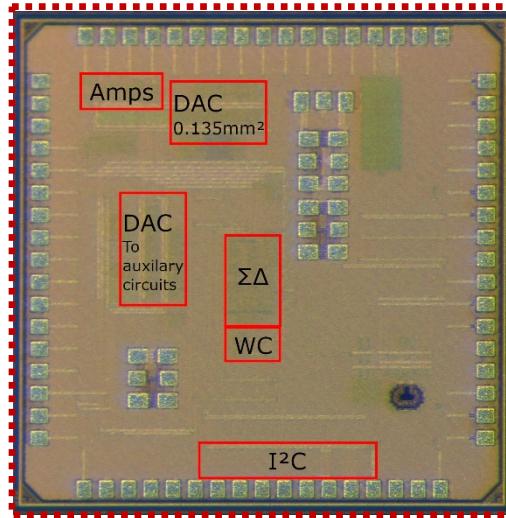
- TSMC 65nm CMOS technology
- Bias DAC duplicate for measurement purposes
 - Auxiliary circuits
 - OpAmp buffer/amplifier
 - $\Sigma\Delta$ modulator



Source: Forschungszentrum Jülich GmbH

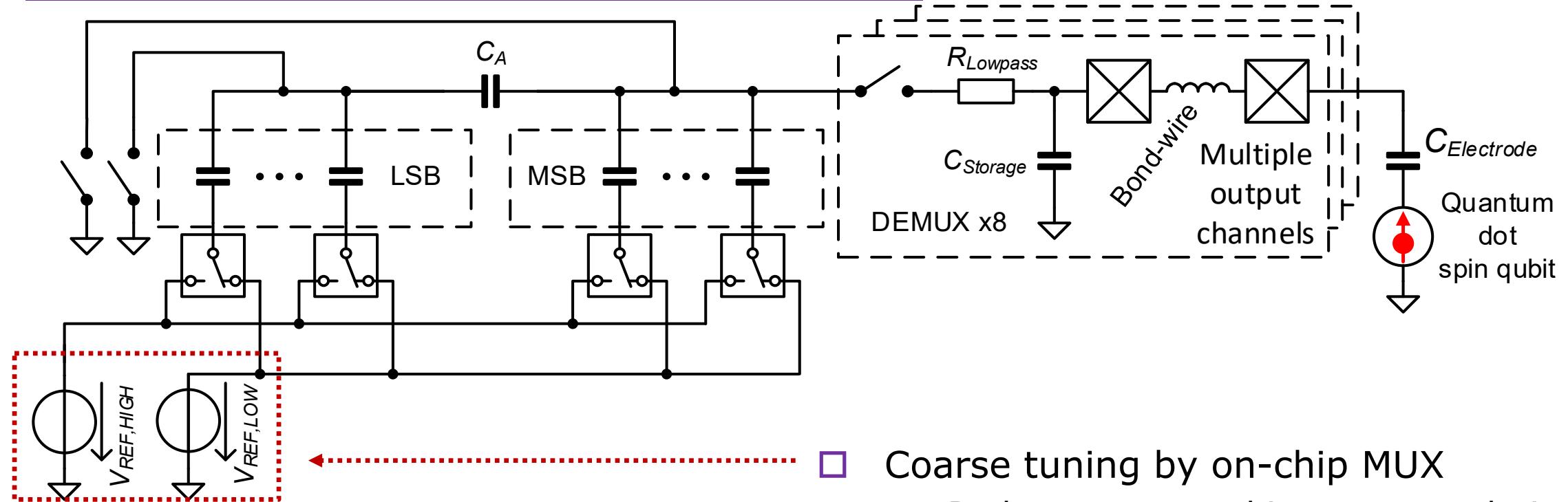
Measurement Setup

- Packaged IC sample inside cryostat
- Cryostat base temperature approx. 6 K



Source: Forschungszentrum Jülich GmbH

Charge-Redistribution Topology



- Negligible static power
- Low thermal noise at cryo. temp.

$$\bar{v}_N^2 = \frac{k_B T}{C}$$

- Coarse tuning by on-chip MUX
 - Reduce power and increase resolution
 - But: need for calibration
- Multiple output channels per DAC
- No output buffer needed
 - Reduce power and noise

Coarse Tuning Reference Voltages

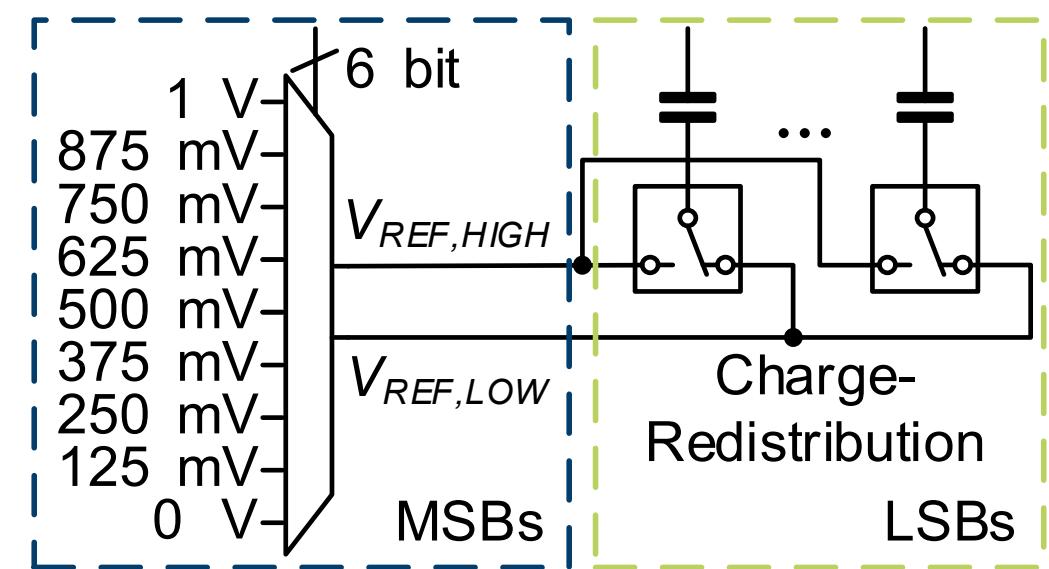
- Coarse tuning by on-chip MUX
 - Reduce dynamic analog power P_{AD}

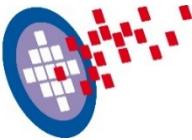
$$\Delta V_{REF} = V_{REF,HIGH} - V_{REF,LOW}$$

$$P_{AD} \propto C_{Total,DAC} \cdot (\Delta V_{REF})^2 \cdot f$$

- $P_{AD} \downarrow$ by $(125 \text{ mV} / 1 \text{ V})^2 = 1/64$

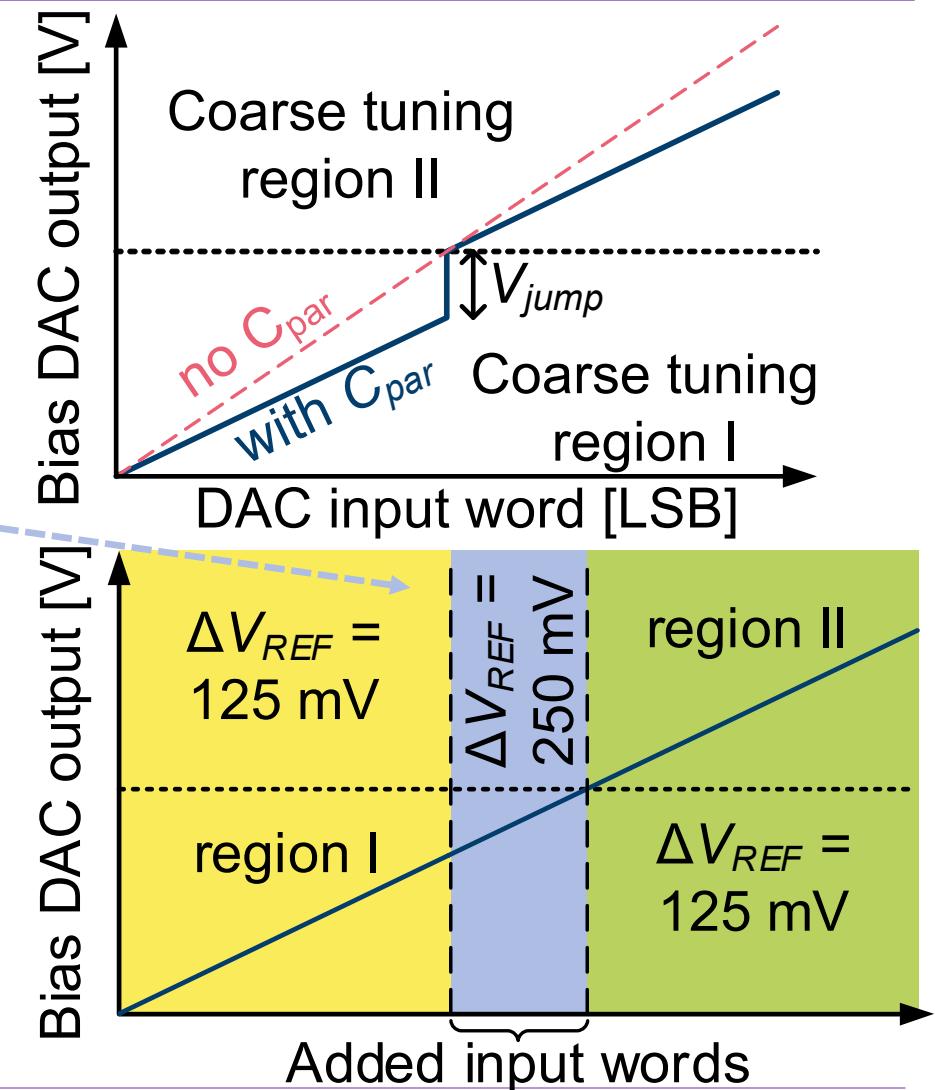
- Resolution increased
 - 3 bit added for VREF,HIGH and VREF,LOW each
 - DAC resolution \uparrow by 3 bit

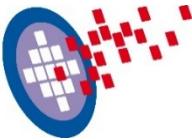




Coarse Tuning Reference Voltages

- Coarse tuning by on-chip MUX
 - Parasitic C_{par} leads to DAC gain < 1
→ Voltage jump V_{jump} at coarse tuning crossings
 - Introduce *intermediate steps*
 - Filling the missing codes range
 - Operated with $\Delta V_{REF} = 250$ mV
 - Add input words
→ Saved in off-chip memory

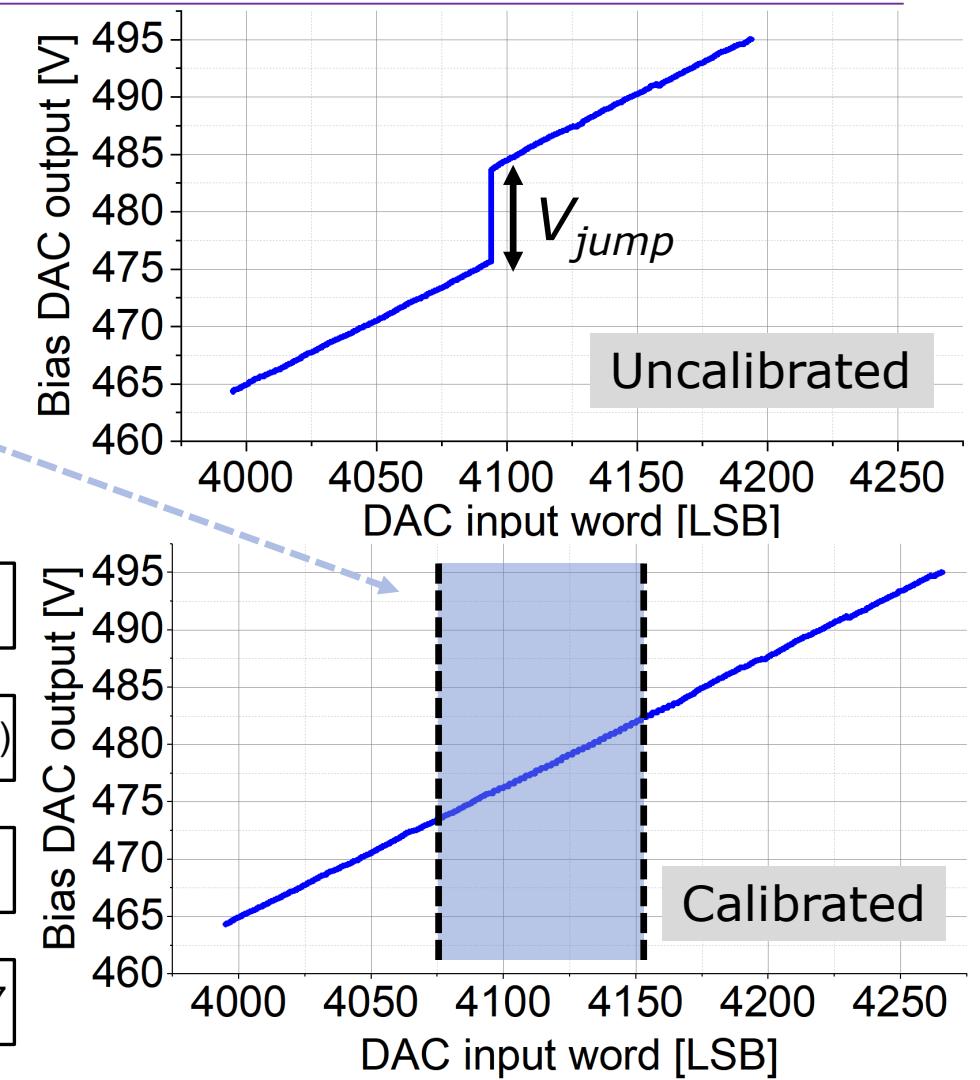




Coarse Tuning Reference Voltages

- Calibration verified at 6 K
 - *Intermediate steps*
 - *Steps doubled*
- Correcting Bias DAC gain

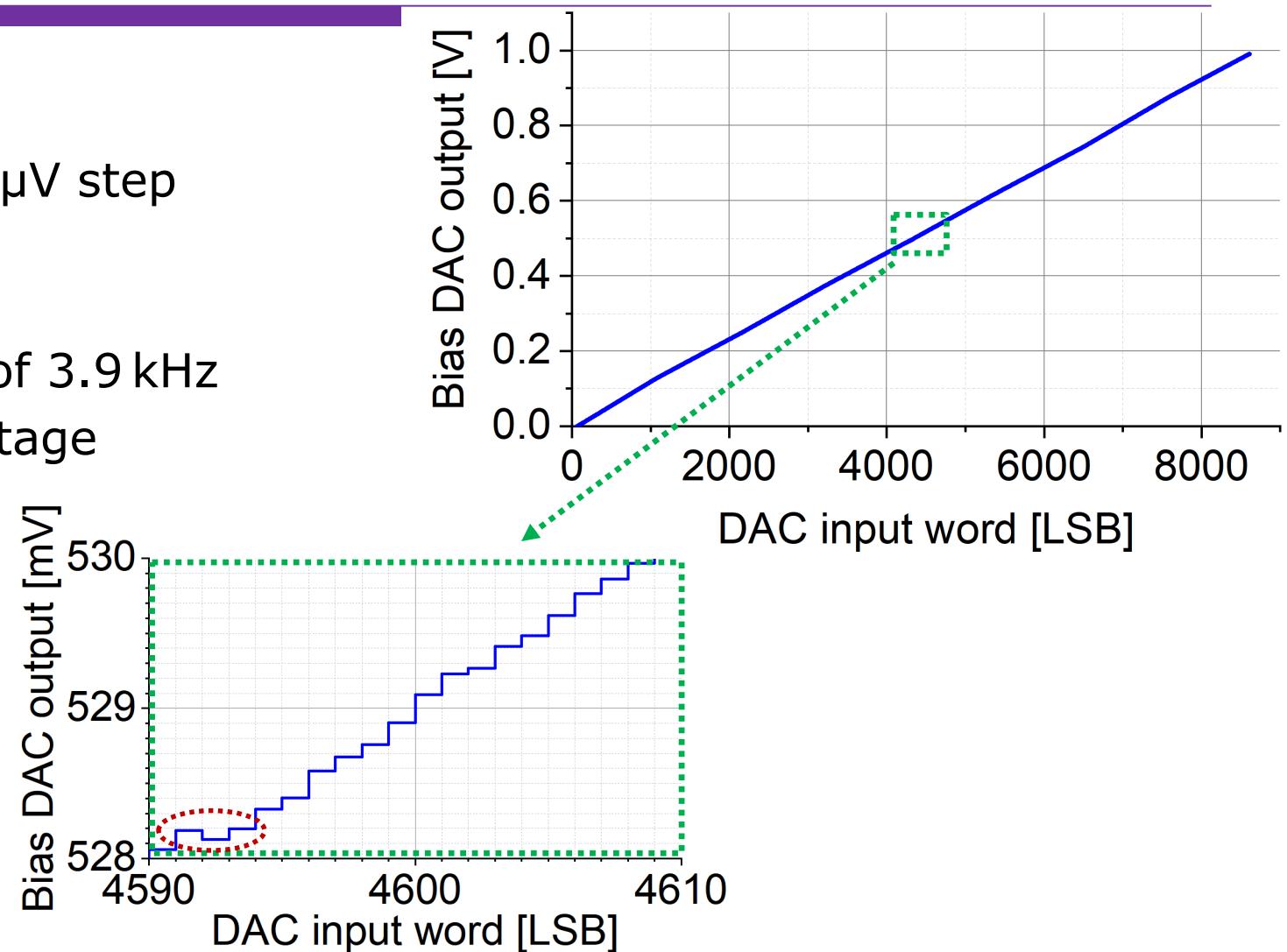
	Intermediate steps range									
$V_{REF,HIGH}$ 3 bit	3 (500 mV)	4 (625 mV)	...	4 (625 mV)						
$V_{REF,LOW}$ 3 bit		3 (375 mV)	...	3 (375 mV)	4 (500 mV)					
Charge-redistribution 10 bit	1022	1023	502	502	503	503	530	530	531	531
Z_{IN}	4094	4095	4096	4097	4098	4099	4152	4153	4154	4155



Bias DAC Results

- Fully functional at 6 K
 - 13 bit resolution ($\approx 120 \mu\text{V}$ step size)
 - 1 V output range
 - Channel refresh rate f_R of 3.9 kHz
 - Calibrated reference voltage coarse tuning

- Singular non-monotonic steps
 - No issue for qubit biasing



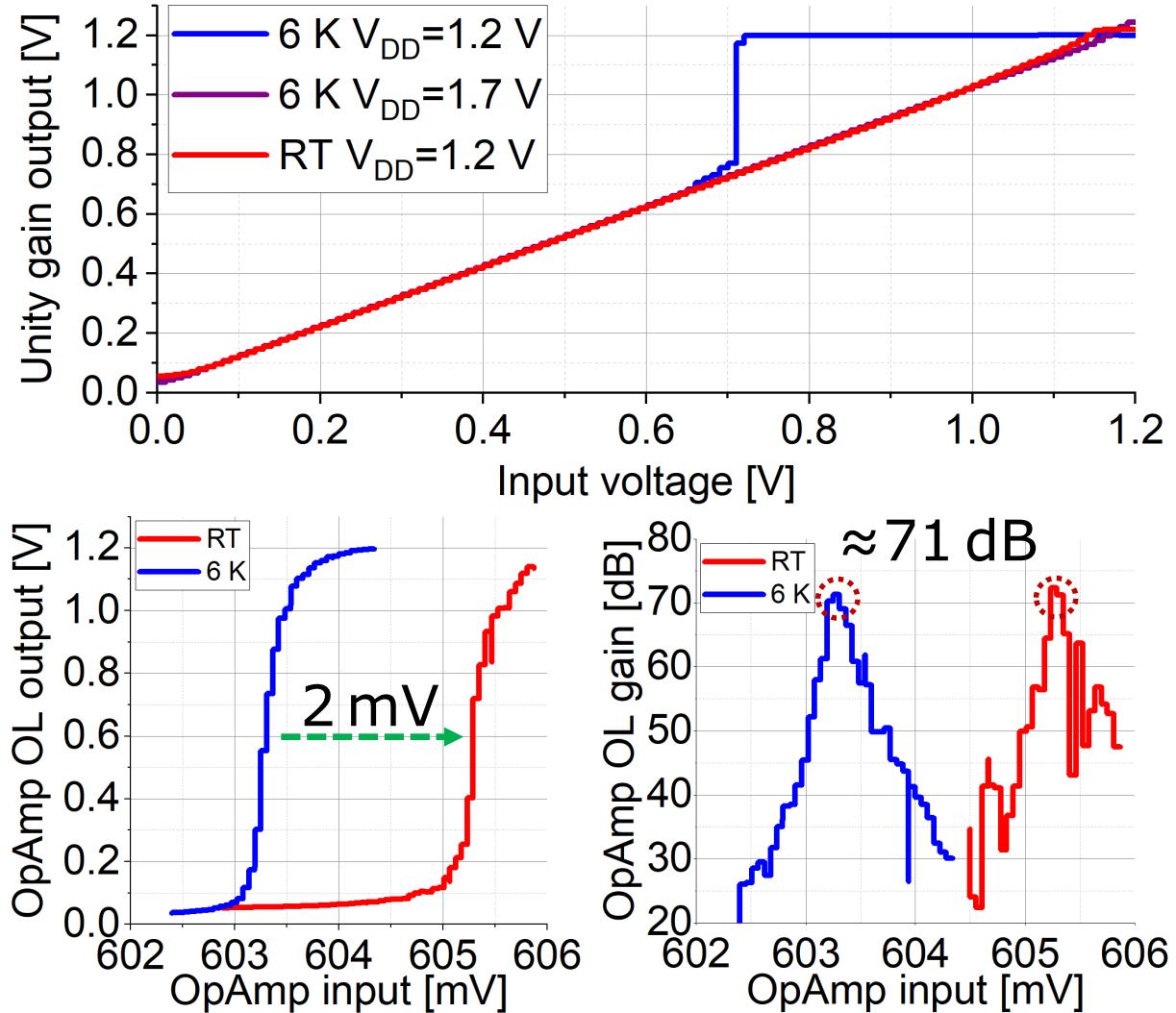
Bias DAC Power Consumption

Bias DAC component	Power Consumption
Analog DAC core (slide 7)	77 nW
Analog DAC reference voltages	3 nW
DAC digital (memory & logic)	21 μ W
DAC total	21.1 μ W (2.63 μ W per channel)
Clock buffer	4.3 μ W
Total	25.4 μ W (3.18 μ W per channel)

- 8 Bias DAC channel running and $f_R = 3.9$ kHz
- Ultra-low power consumption $\approx 3 \mu\text{W}$ per channel
 - Digital part > 99% \rightarrow Scales well with CMOS technology

OpAmp Results

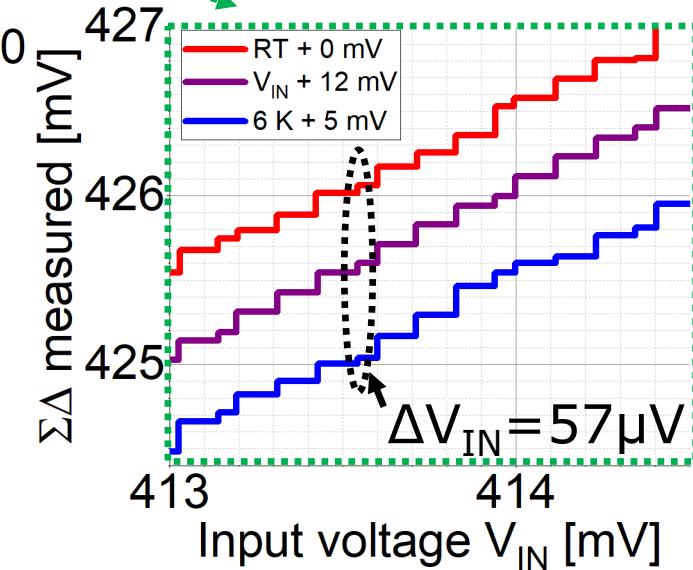
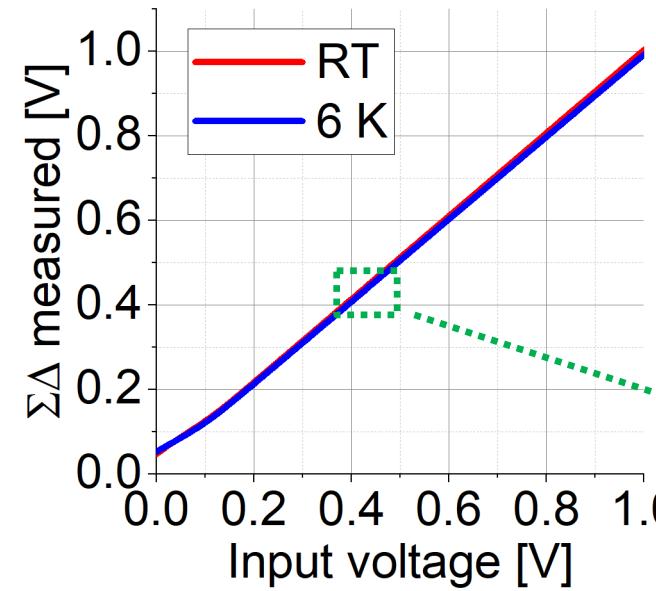
- Unity gain configuration
- Enable Bias DAC noise measurement
- Supply increase: 1.2 V to 1.7 V at 6 K
- Small offset voltage shift of $\approx 2 \text{ mV}$ 
- Comparable open-loop (OL) gain of $\approx 71 \text{ dB}$ 



$\Sigma\Delta$ Modulator Results

- Measurement at 6 K
- On-chip analog-to-digital conversion
 - 3rd order 2-1 MASH modulator

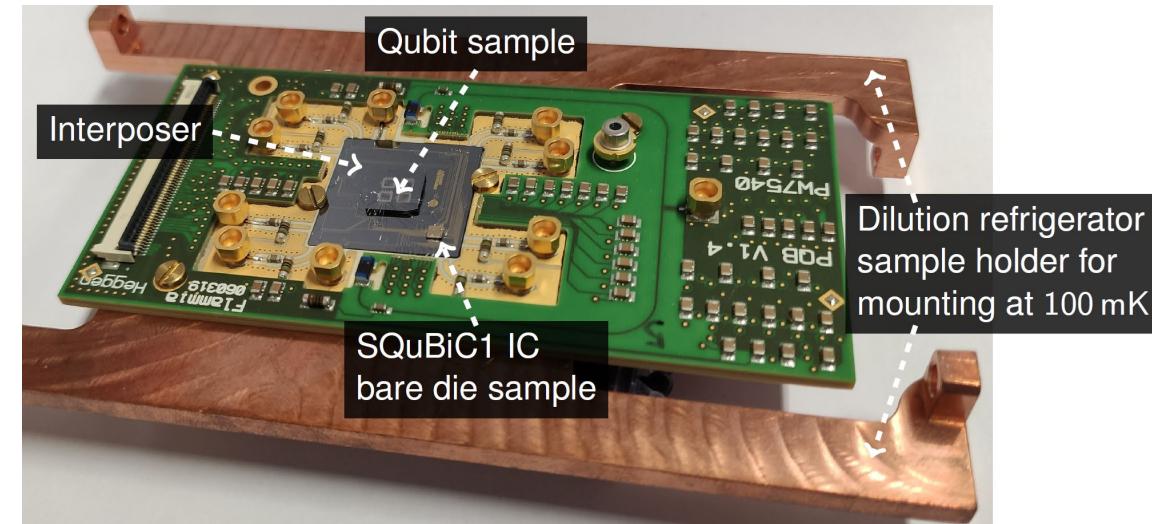
- Off-chip bit-stream filtering
- Building block for future on-chip Bias DAC calibration



Summary & Outlook

- Prototype IC for local qubit biasing
 - Incl. additional measurement and support circuitry
 - All circuits are tuned operational at 6 K
 - Bias DAC power $\approx 3 \mu\text{W}$ per channel

- Next steps:
 - Ongoing effort to test with a qubit sample
 - (Prof. Bluhm's group at RWTH Aachen)
 - IC sample on 100 mK interposer



Source: Forschungszentrum Jülich GmbH

- [1] Vandersypen, L.M.K., Bluhm, H., Clarke, J.S. *et al.* Interfacing spin qubits in quantum dots and donors—hot, dense, and coherent. *npj Quantum Inf* **3**, 34 (2017). <https://doi.org/10.1038/s41534-017-0038-y>
- P. Vliex et al., "Bias Voltage DAC Operating at Cryogenic Temperatures for Solid-State Qubit Applications," in IEEE Solid-State Circuits Letters, vol. 3, pp. 218-221, 2020, doi: 10.1109/LSSC.2020.3011576.